

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Thermal characteristics

Thermal resistance, junction - minimal footprint	R_{thJA}		-	-	350	K/W
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Electrical characteristics, at $T_j=25\text{ °C}$, unless otherwise specified

Static characteristics

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{ V}, I_D=250\text{ }\mu\text{A}$	240	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=0\text{ V}, I_D=56\text{ }\mu\text{A}$	0.8	1.4	1.8	
Drain-source leakage current	$I_{D(off)}$	$V_{DS}=240\text{ V}, V_{GS}=0\text{ V}, T_j=25\text{ °C}$	-	-	0.01	μA
		$V_{DS}=240\text{ V}, V_{GS}=0\text{ V}, T_j=150\text{ °C}$	-	-	5	
Gate-source leakage current	I_{GSS}	$V_{GS}=20\text{ V}, V_{DS}=0\text{ V}$	-	-	10	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=4.5\text{ V}, I_D=0.09\text{ A}$	-	9.07	20	Ω
		$V_{GS}=10\text{ V}, I_D=0.1\text{ A}$	-	7.7	14	
Transconductance	g_{fs}	$ V_{DS} >2 I_D R_{DS(on)max}, I_D=0.08\text{ A}$	0.06	0.13	-	S

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Dynamic characteristics

Input capacitance	C_{iss}	$V_{GS}=0\text{ V}, V_{DS}=25\text{ V},$ $f=1\text{ MHz}$	-	58	77	pF
Output capacitance	C_{oss}		-	7.3	10	
Reverse transfer capacitance	C_{rss}		-	2.8	4.2	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=120\text{ V},$ $V_{GS}=10\text{ V}, I_D=0.1\text{ A},$ $R_G=6\ \Omega$	-	3.3	5.0	ns
Rise time	t_r		-	3.1	4.6	
Turn-off delay time	$t_{d(off)}$		-	13.7	20	
Fall time	t_f		-	64.5	97	

Gate Charge Characteristics

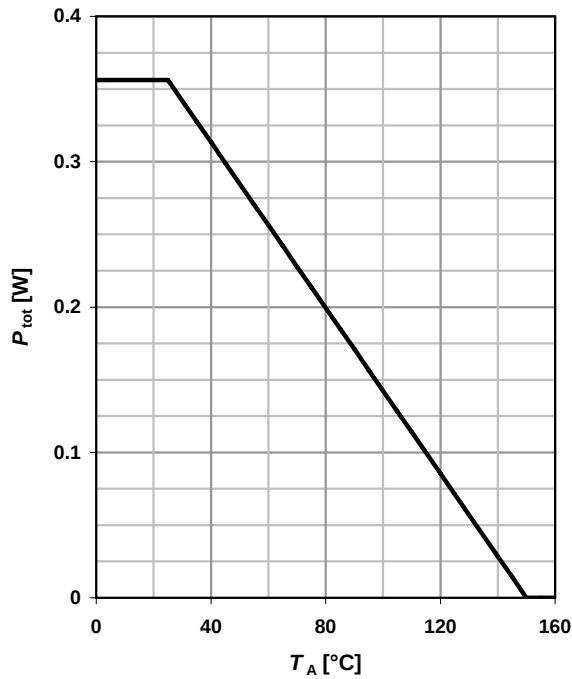
Gate to source charge	Q_{gs}	$V_{DD}=192\text{ V}, I_D=0.1\text{ A},$ $V_{GS}=0\text{ to }10\text{ V}$	-	0.16	0.22	nC
Gate to drain charge	Q_{gd}		-	0.8	1.2	
Gate charge total	Q_g		-	2.1	3.1	
Gate plateau voltage	$V_{plateau}$		-	2.90	-	V

Reverse Diode

Diode continuous forward current	I_S	$T_A=25\text{ °C}$	-	-	0.11	A
Diode pulse current	$I_{S,pulse}$		-	-	0.43	
Diode forward voltage	V_{SD}	$V_{GS}=0\text{ V}, I_F=0.1\text{ A},$ $T_j=25\text{ °C}$	-	0.81	1.2	V
Reverse recovery time	t_{rr}	$V_R=120\text{ V}, I_F=0.1\text{ A},$ $di_F/dt=100\text{ A}/\mu\text{s}$	-	42.9	64.3	ns
Reverse recovery charge	Q_{rr}		-	22.6	34	

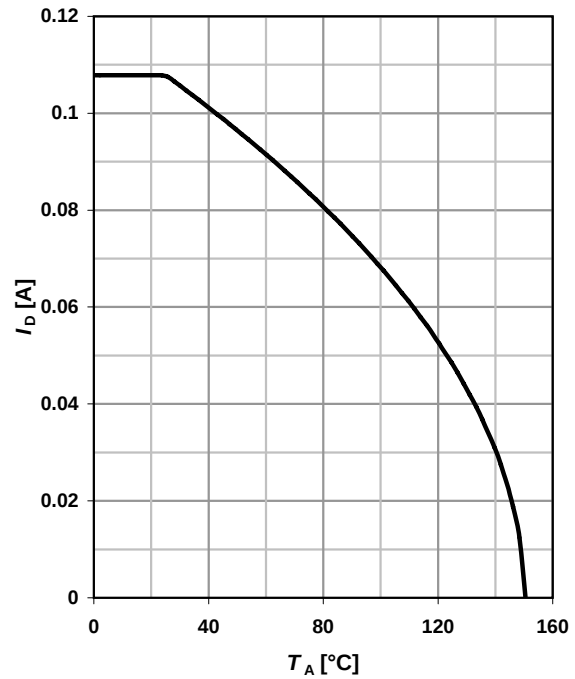
1 Power dissipation

$$P_{\text{tot}} = f(T_A)$$



2 Drain current

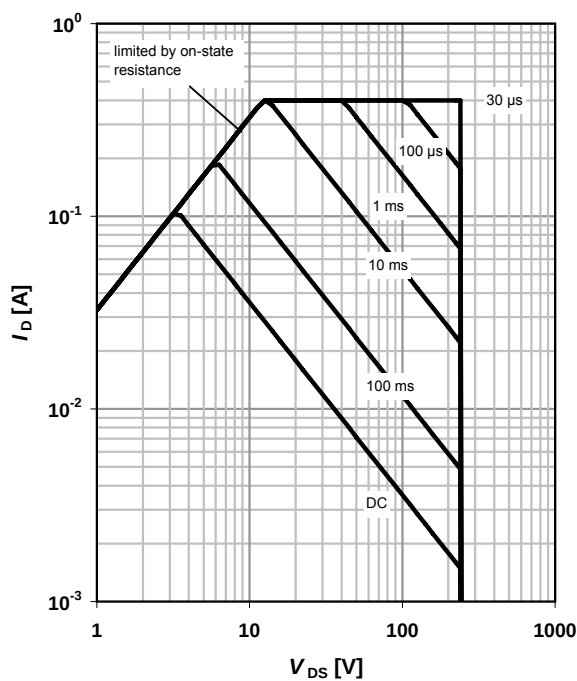
$$I_D = f(T_A); V_{\text{GS}} \geq 10 \text{ V}$$



3 Safe operating area

$$I_D = f(V_{\text{DS}}); T_A = 25^\circ\text{C}; D = 0$$

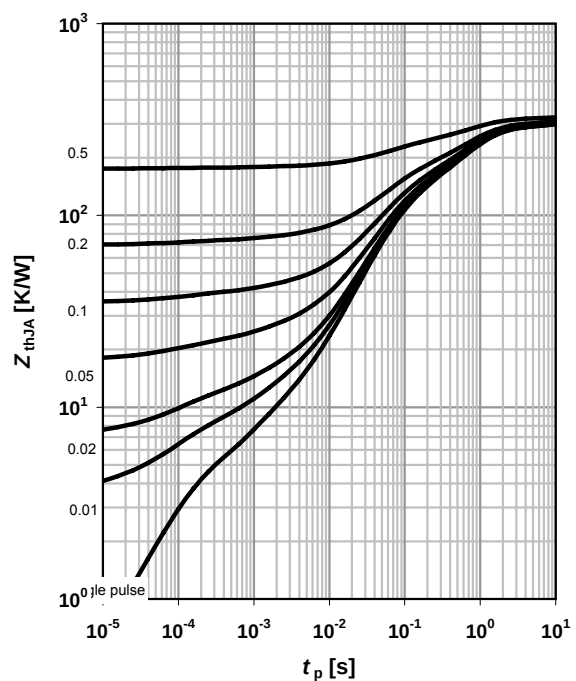
parameter: t_p



4 Max. transient thermal impedance

$$Z_{\text{thJA}} = f(t_p)$$

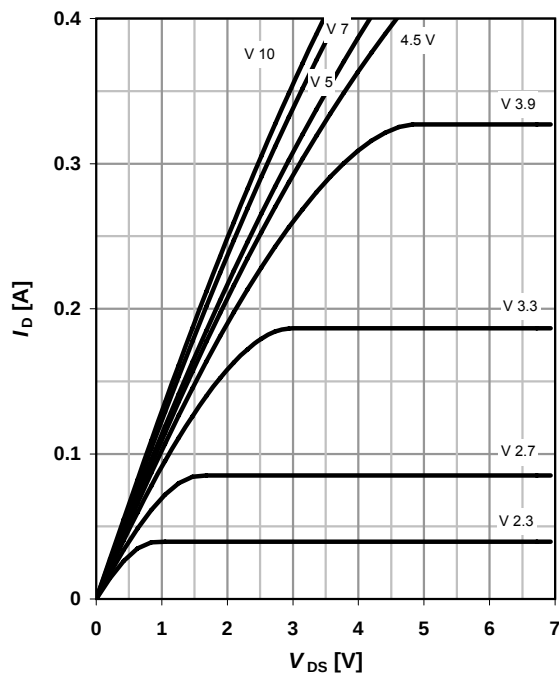
parameter: $D = t_p/T$



5 Typ. output characteristics

$$I_D = f(V_{DS}); T_J = 25^\circ\text{C}$$

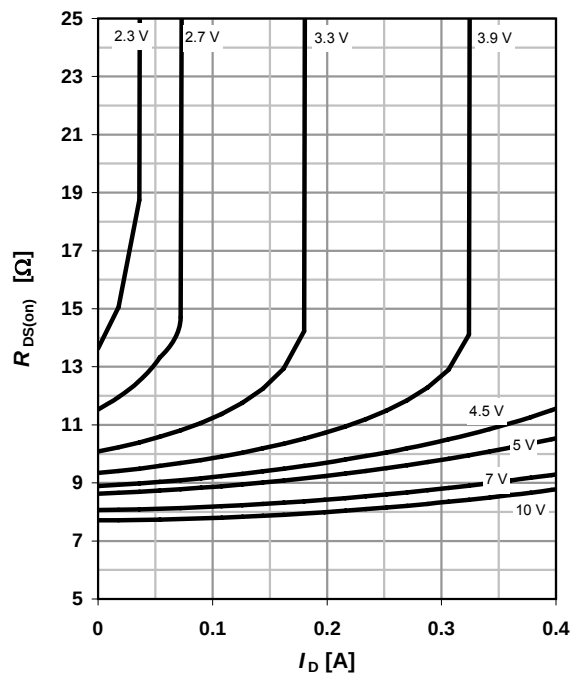
parameter: V_{GS}



6 Typ. drain-source on resistance

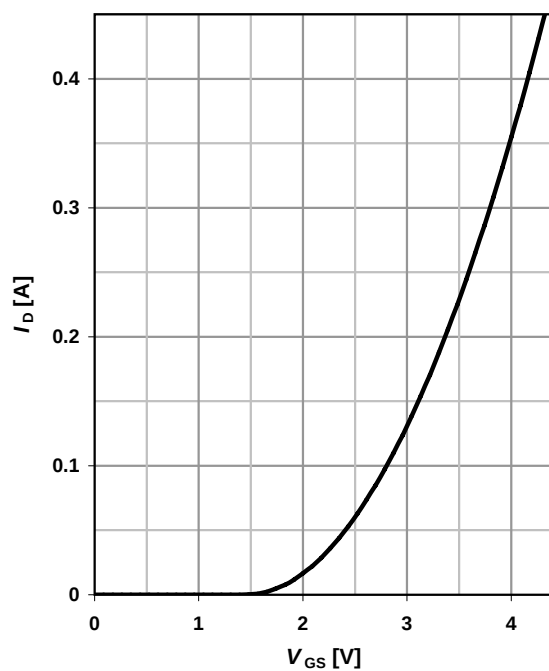
$$R_{DS(on)} = f(I_D); T_J = 25^\circ\text{C}$$

parameter: V_{GS}



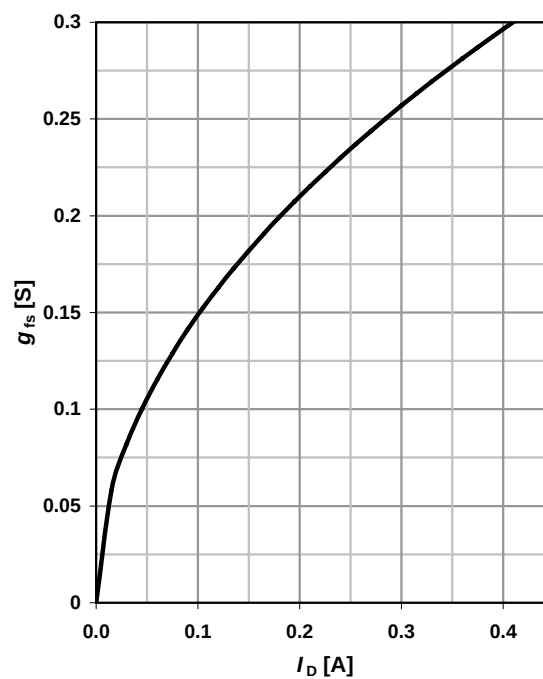
7 Typ. transfer characteristics

$$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}$$



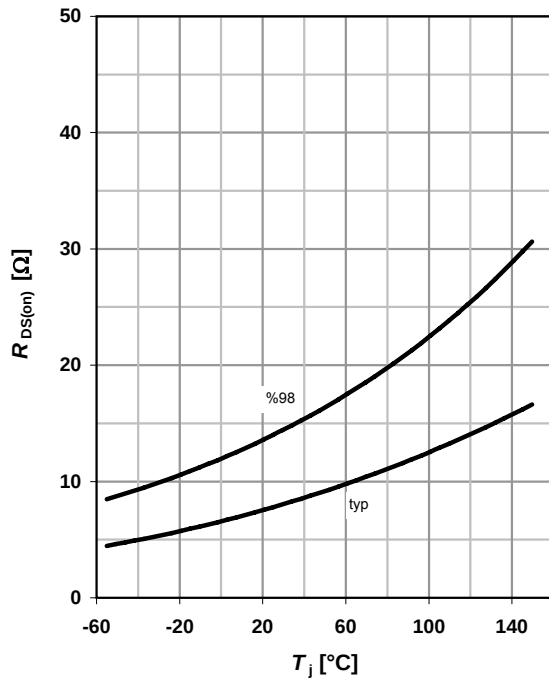
8 Typ. forward transconductance

$$g_{fs} = f(I_D); T_J = 25^\circ\text{C}$$



9 Drain-source on-state resistance

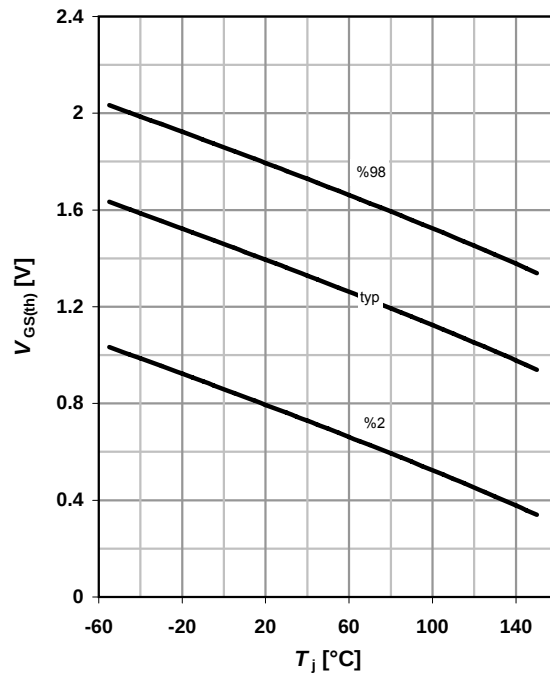
$$R_{DS(on)} = f(T_j); I_D = 0.1 \text{ A}; V_{GS} = 10 \text{ V}$$



10 Typ. gate threshold voltage

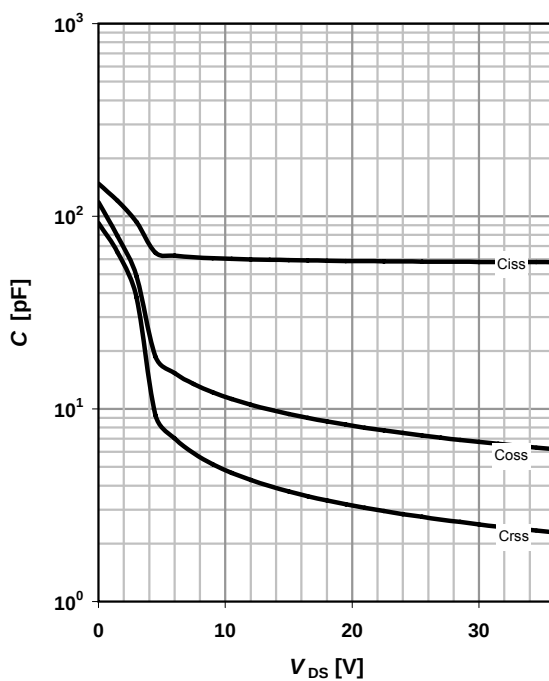
$$V_{GS(th)} = f(T_j); V_{DS} = V_{GS}; I_D = 56 \text{ μA}$$

parameter: I_D



11 Typ. capacitances

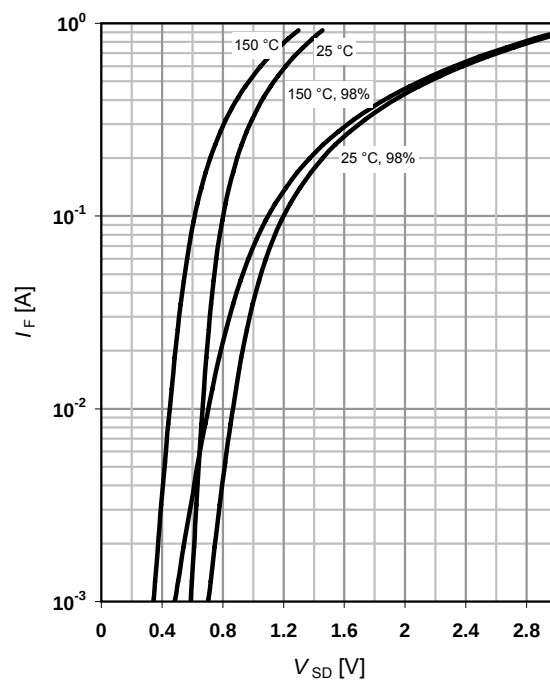
$$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}; T_j = 25^\circ\text{C}$$



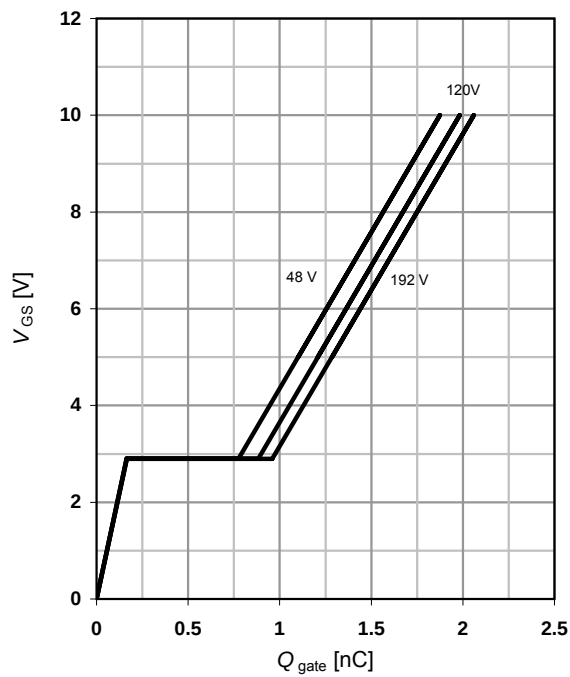
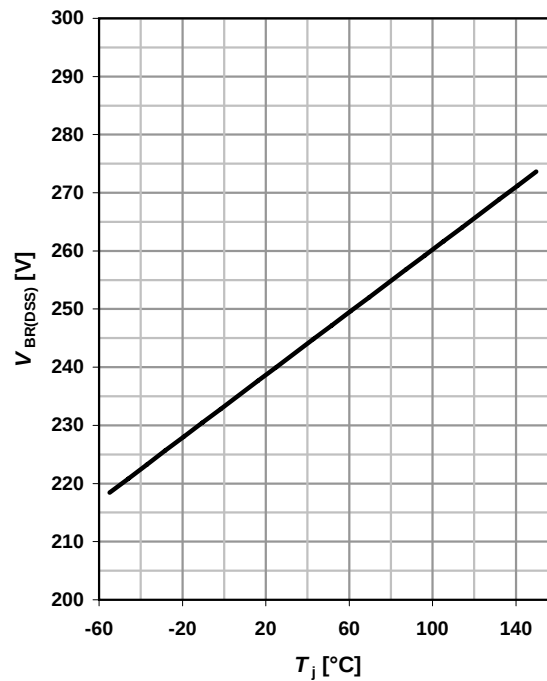
12 Forward characteristics of reverse diode

$$I_F = f(V_{SD})$$

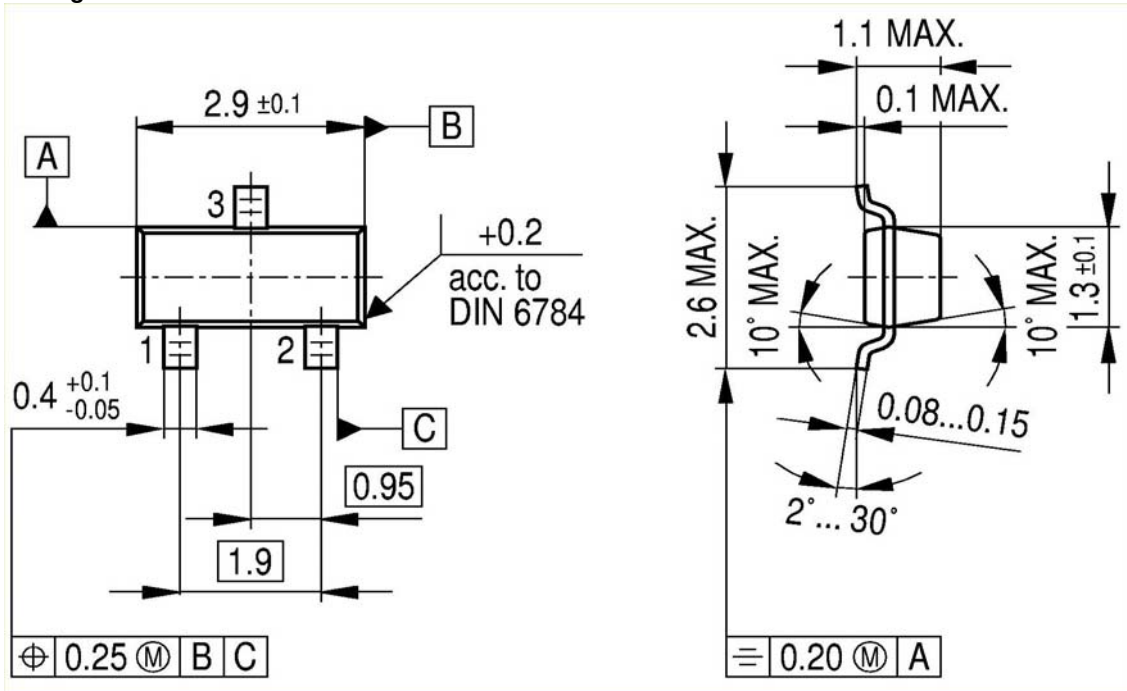
parameter: T_j



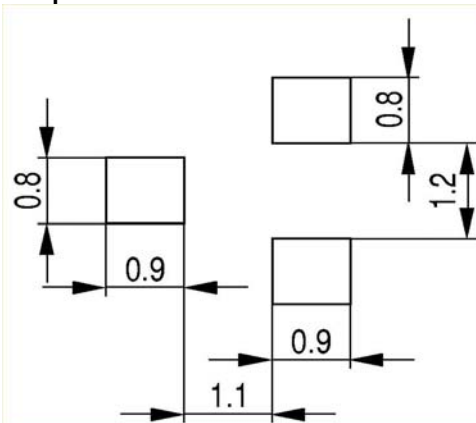
13 Typ. gate charge
 $V_{GS}=f(Q_{gate}); I_D=0.1 \text{ A pulsed}$

parameter: V_{DD}

14 Drain-source breakdown voltage
 $V_{BR(DSS)}=f(T_j); I_D=250 \text{ }\mu\text{A}$


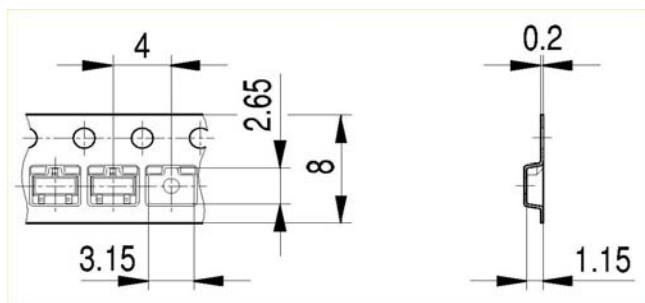
Package Outline:



Footprint:



Packaging:



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